



Introduction to Nanophotonics

Logan Liu Micro and Nanotechnology Lab Department of Electrical & Computer Engineering University of Illinois

What is Nanophotonics?

This area of nanoscience, called *nanophotonics*, *is* defined as "the science and engineering of light matter interactions that take place on wavelength and subwavelength scales where the physical, chemical or structural nature of natural or artificial nanostructured matter controls the interactions"

---National Academy of Science





ECE ILLINOIS

Early Examples of Nanophotonics





Nanophotonics in Mother Nature



Foundation of Nanophotonics

• Photon-Electron Interaction and Similarity



Moving charges create electric fields \rightarrow Creation of light Electric fields make charges move \rightarrow Detection of light

"There's Plenty of Room at the Bottom" (Feynman, 1961)

Foundation of Nanophotonics

Basic Equations describing propagation of photons in dielectrics has some similarities to propagation of electrons in crystals

Similarities between Photons and Electrons

Wavelength of Light, $\lambda = \frac{h}{n} = \frac{c}{v}$

Wavelength of Electrons,

$$\lambda = \frac{h}{p} = \frac{h}{mv}$$

Foundation of Nanophotonics

Maxwell's Equations for Light

$$\nabla \times H = \frac{1}{c} \frac{\partial D}{\partial t} \qquad \nabla \times E = \frac{-1}{c} \frac{\partial B}{\partial t}$$

Eigenvalue Wave Equation:
$$\nabla \times [\mu^{-1} \nabla \times E(r)] = \omega^2 \varepsilon E(r)$$
$$\nabla \times [\varepsilon^{-1} \nabla \times H(r)] = \omega^2 \mu H(r)$$

For plane wave $\nabla \cdot \nabla E(r) = \varepsilon k_0^2 E(r)$

Describes the allowed frequencies of light

Schrodinger's Eigenvalue Equation for Electrons:

$$\frac{-(\frac{h^2}{4\pi^2})}{2m} [\nabla \cdot \nabla + V(r)]\psi(r) = E\psi(r)$$

Describes allowed Energies of Electrons

Foundation of Nanophotonics Free Space Solutions:

Photon Plane Wave: $E = E^0 \left(e^{ik.r - \omega t} + e^{-ik.r + \omega t} \right)$

Electron Plane Wave:
$$\Psi = c \left(e^{ik.r - \omega t} + e^{-ik.r + \omega t} \right)$$

Interaction Potential in a Medium:

Propagation of Light affected by the Dielectric Medium (refractive index)

Propagation of Electrons affected by Coulomb Potential

Foundation of Nanophotonics

Photon tunneling through classically forbidden zones. E and B fields decay exponentially. k-vector imaginary.



Planar Waveguide, n₁>n₂



Wavefunction for a particle in a Potential Well

Electron Wavefunction decays exponentially in forbidden zones



Foundation of Nanophotonics

Confinement of Light results in field variations similar to the confinement of Electron in a Potential Well. For Light, the analogue of a Potential Well is a region of high refractive-index bounded by a region of lower refractive-index.



Nanoscale Confinement of Electrons

Thin film-Quantum Well 1 D Confinement

Quantum Wire: 2-D Confinement



Quantum Dot: 3-D Confinement

Foundation of Nanophotonics

- Free space propagation of both electrons and photons can be described by Plane Waves.
- Momentum for both electrons and photons, $\mathbf{p} = (h/2\pi)\mathbf{k}$
- For Photons, $k = (2\pi/\lambda)$ while for Electrons, $k = (2\pi/h)mv$
- For Photons, Energy $E = pc = (h/2\pi)kc$ while for Electrons,

 $E = p^2/2m = (h/2\pi)^2k^2/2m$



Near Field Optics In Far-Field Microscopy, Resolution = $1.22 \left(\frac{\lambda}{2NA}\right)$

This can be overcome with Near-Field Techniques by having nanoscale apertures or by using aperture-less techniques which enhance light interaction over nanoscale dimensions with the use of nanoscale tips, nanospheres etc. The idea of using sub-wavelength aperture to improve optical resolution was first proposed by Synge in a letter to Einstein in 1928. These ideas were implemented into optics much later in 1972 [Ash and Nicholls]

> Schematic set-ups for Near-Field Scanning Optical Microscope (NSOM)



Near-Field Optics



Tip collects the evanescent light created by laser illuminating the sample from the back

SNOM



Tip illuminates the sample; Scattered light is collected

ECE ILLINOIS

Near Field Optics

L

Model of far- or near-field, Left: Slit,illuminated with plane wave Right: sub-wacelength aperture.

 $z = \varepsilon << \lambda$, Then Eqn. (1) is recaptured by $Z \to \varepsilon$ ture.

Then taking at aperture, $f(x, z = \varepsilon) = rect(\frac{x}{\omega})$

Now far field: $f(x, z = Z) = \int_{-\frac{\omega}{2\pi C}}^{\frac{\omega}{2\pi C}} d\alpha_x \{ e^{-i2\pi\alpha_x x} e^{-i2\pi\sqrt{\alpha^2 - \alpha_x^2}(Z-\varepsilon)} \times \int_{-\infty}^{\infty} d\alpha_x^{"} e^{-i2\pi\alpha_x^{"} x} F(\alpha_x^{"}, z = 0) \frac{\sin((\alpha_x - \alpha_x^{"})w)}{\alpha_x - \alpha_x^{"}} \cdot e^{-2\pi\sqrt{\alpha^2 - \alpha_x^{"} \varepsilon}} \} \cdots (3)$

 $F(\alpha_x, z=0) = E_o \delta(\alpha_x - K)$, with K one spatial frequency

Near Field Optics

Continued from the previous page

 $Eqn.(1) \Rightarrow f(x, z = Z) = E_o e^{-i2\pi Kx} \cdot e^{-i2\pi \sqrt{\alpha^2 - K^2}Z} \qquad \text{for } K < \omega / C$ $= 0, \qquad \qquad \text{for } K > \omega / C \qquad \cdots (4)$

$$Eqn.(3) \Rightarrow f(x, z = Z) = E_o e^{-i2\pi\sqrt{\alpha^2 - K^2}\varepsilon} \int_{-\frac{\omega}{2\pi C}}^{\frac{\omega}{2\pi C}} d\alpha_x e^{-i2\pi\alpha_x x} e^{-i2\pi\sqrt{\alpha^2 - \alpha_x^2}(Z-\varepsilon)} \frac{\sin(\alpha_x - K)w}{\alpha_x - K} \cdots (5)$$

Notes: Eqn. (4) fulfills all our notions about far-field microscope and its inability to carry information beyond certain spatial frequency

Eqn. (5) integral doesn't vanish for $K > \omega / C$, such that high-frequency elements still contribute to the signal arriving at z=Z (far field).

Eqn. (4) collapses to (5) when w (aperture width) is large, i.e. $\frac{\sin(\alpha_x - K)w}{\alpha_x - K} \rightarrow \delta(\alpha_x - K)$

In the near-field, evanescent terms must be taken into account, due to the convolution of the tip and the sample.

Quantum confinement

Quantum-confined materials refer to structures which are constrained to nanoscale lengths in one, two or all three dimensions. The length along which there is Quantum confinement must be small than de Broglie wavelength of electrons for thermal energies in the medium.

Thermal Energy, E = $\frac{\mathbf{mv}^2}{2} = \mathbf{kT}$ de Broglie Wavelength, $\lambda = \frac{\mathbf{h}}{\mathbf{mv}} = \frac{h}{\sqrt{2mkT}}$

Material	Electron effective mass	Hole effective mass		
Group IV				
<u>Si</u> (4.2K)	1.08 me	0.56 me		
Ge	0.55 me	0.37 me		
III-V				
<u>GaAs</u>	0.067 m _e	0.45 me		
<u>InSb</u>	0.013 me	0.6 me		
II-VI				
ZnO	0.19 me	1.21 me		
ZnSe	0.17 <i>m</i> e	1.44 me		

For T = 10 K, the calculated λ in GaAs is 162 nm for Electrons and 62 nm for Holes

For effective Quantum-confinement, one or more dimensions must be less than 10 nm. Structures which are Quantumconfined show strong effect on their Optical Properties. Artificially created structures with Quantum-confinement on one, two or three dimensions are called, Quantum Wells, Quantum Wires and Quantum Dots respectively.

ECE ILLINOIS

Quantum Confinement

Nanoscale Confinement in 1-Dimension results in a "Quantum Well"



At 300 K, The band gap of GaAs is 1.43 eV while it is 1.79 eV for AlxGa1-xAs (x=0.3). Thus the electrons and holes in GaAs are confined in a 1-D potential well of length L in the Z-direction.



Quantization of energy into discrete levels has applications for fabrication of new solidstate lasers. Two or more Quantum wells side-by-side give rise to Multiple Quantum Wells (MQM) structure.

Motion is confined only in the Zdirection. For electrons and holes moving in the Z-direction in low bandgap material, their motion can be described by <u>Particle in a Box.</u> If the depth of Potential Well is V, for energies E<V, we can write,

$$E_{n,k_x,k_y} = E_C + \frac{n^2 h^2}{8m_e^* L^2} + \frac{h^2 (k_x^2 + k_y^2)}{8\pi^2 m_e^*}$$

n = 1, 2, 3,....

 $p_x = (h/2\pi)k_x$ and $p_y = (h/2\pi)k_y$ can take continuous value and m_e^* is the effective mass of electron

dN/dE

Density

Energy, E

Quantum Confinement

GaAs

MrGa1-xA

M_xGa_{1-x}As

Quantum Well: 1D Confinement

ECE ILLINOIS

Due to 1-D confinement, the number of continuous energy states in the 2-D phase space satisfy

$$2mE_{2D} = p_x^2 + p_y^2$$

Quantum Wire: 2D Confinement

2D confinement in X and Z directions. For wires (e.g. of InP, CdSe). with rectangular cross-section, we can write:

$$E_{n_1,n_2,k_y} = E_C + \frac{n_1^2 h^2}{8m_e^* L_x^2} + \frac{n_2^2 h^2}{8m_e^* L_z^2} + \frac{h^2 k_y^2}{8\pi^2 m_e^*}$$

Quantum Dot: 3D Confinement

For a cubical box with the discrete energy levels are given by:

$$E_{n_1,n_2,n_3} = E_C + \frac{h^2}{8m_e^*} \left(\frac{n_1^2}{L_x^2} + \frac{n_2^2}{L_y^2} + \frac{n_3^2}{L_z^2}\right)$$



Quantum Confinement

Size Dependence of Optical Properties

In general, confinement produces a blue shift of the band-gap. Location of discrete energy levels depends on the size and nature of confinement.

Increase of Oscillator Strengths

This implies increase of optical transition probability. This happens anytime the energy levels are squeezed into a narrow range, resulting in an increase of energy density. The oscillator strengths increase as the confinement increases from Bulk to Quantum Well to Quantum Wire to Quantum Dot.

Computational Nanophotonics

- Analytical approach hampered by over-simplifying assumptions
 - Perfect conductivity, zero thickness materials, semi-infinite structures, ...
- Frequency vs. Time domain?
- Computational resources becoming less constraining
 - Very complex problems being tackled
- Finite Difference Time Domain (FDTD)
- Frequency Domain Integral-differential

Computational Nanophotonics

Time Domain

- Numerical integration of Ampere/Faraday
- Impulse excitation
- Numerical integration to get steady state
- Relate time series to frequency domain via F.T.
- Some problems with highly dispersive *media* (convolutional response)
- No big things to invert but lots of memory
- Sophisticated variable mesh

Frequency Domain

- Time harmonic excitation (steady state)
- Boundary value problem based
 on integro-differential equation
- Big things to invert (stability/accuracy issues possible)
- Relate to time domain by F.T.

ECE ILLINOIS

Finite Difference Time Domain (FDTD) Yee Cell – Space/Time



$$E_{x}(n+1,i,j,k) = E_{x}(n,i,j,k) + \frac{\Delta t}{\varepsilon(i,j,k)} \left\{ \frac{H_{z}(n+\frac{1}{2},i,j+\frac{1}{2},k) - H_{z}(n+\frac{1}{2},i,j-\frac{1}{2},k)}{\Delta y} - \frac{H_{y}(n+\frac{1}{2},i,j,k+\frac{1}{2}) - H_{y}(n+\frac{1}{2},i,j,k-\frac{1}{2})}{\Delta z} \right\}$$



Static State Computation



ECE ILLINOIS

Solve Laplace equation

$$\frac{1}{\rho} \frac{\partial}{\partial \rho} \left(\rho \frac{\partial \Phi}{\partial \rho} \right) + \frac{1}{\rho^2} \frac{\partial^2 \Phi}{\partial \theta^2} = 0$$

Charge density

$$\sigma(\rho) = \varepsilon E(\rho, 0) = \frac{\varepsilon \pi a}{\beta} \rho^{(\pi/\beta) - 1}$$

Singularity near the sharp tip

$$\beta > \pi \Longrightarrow \sigma(\rho \to 0) \to \infty$$

Finite Element Simulation



Solve Harmonic Wave Equation

 $\nabla \times (\mu^{-1} \nabla \times E) - \omega^{2} \varepsilon E = 0$ $\nabla \times (\varepsilon^{-1} \nabla \times H) - \omega^{2} \mu H = 0$ For Plane Wave $\nabla \cdot \nabla E_{z} - \varepsilon k_{0}^{2} E_{z} = 0$ $-\nabla \cdot (\varepsilon \nabla H_{z}) - k_{0}^{2} H_{z} = 0$

Low-reflecting Boundary Condition

 $n \times \sqrt{\mu}H + \sqrt{\varepsilon}E_{z} = 2\sqrt{\varepsilon}E_{0z}$ $n \times \sqrt{\varepsilon}E - \sqrt{\mu}H_{z} = -2\sqrt{\mu}H_{0z}$



Plasmonics



Transverse EM wave coupled to a plasmon (wave of charges on a metal/dielectric interface) = SPP (surface plasmon polariton)

Note: the wave has to have the component of E transverse to the surface (be TM-polarized).

Polariton – any coupled oscillation of photons and dipoles in a medium





Plasmonics Research



Details in Prof. Nick Fang's Lecture

ECE ILLINOIS

Metamaterials



Air Metamaterial Air n=1 n=-1 n=1 Point Internal Focus | d/2 l d d/2 l







Hormann et al, Optics Express (2007)

- Engineered material responses, electrical permittivity ε(ω) and magnetic permeability μ(ω).
 - Fields of individual nanostructures,
 - subwavelength scale, "effective medium limit"
 - resonant response to electric or magnetic field
- Possible to design metamaterials with a magnetic response at optical frequencies that no known natural material exhibits
- "Negative" Refractive index $n_1 \sin(\theta_1) = n_2 \sin(\theta_2)$
- Applications: Detection, Switching, Modulation of light, Engineered birefringence.







Details in Prof. Nick Fang's Lecture

ECE ILLINOIS

Photonic Crystal

The most striking similarity is the **Band-Gap** within the spectra of Electron and Photon Energies



Electronic Crystal

Solution of Schroedinger's equation in a 3D periodic coulomb potential for electron crystal forbids propagation of free electrons with energies within the Energy Band-Gap.



Likewise, diffraction of light within a Photonic Crystal is forbidden for a range of frequencies which gives the concept of Photonic Band-Gap. The forbidden range of frequencies depends on the direction of light with respect to the photonic crystal lattice. However, for a sufficiently refractive-index contrast (ratio n1/n2), there exists a Band-Gap which is omni-directional.

ECE ILLINOIS

Photonic Crystal

NATURAL





1D Photonic Crystal (Bragg grating and thin film stack)



two directions

periodic in three directions

2D Photonic Crystal PLANAR WAVEGUIDE

-1,5 µm

3D PHOTONIC CRYSTAL



OPTICAL FIBER

2D Photonic Crystal

MICROSTRUCTURED

ECE ILLINOIS



I

All-Optical Processor



Molecular Nanophotonics

- Bridge between current photonic systems and future approaches bringing in, eg:
 - Access to further integration
 - Lower noise

• Moving towards molecular photonics as the probable limit of integration which:

- will dissipate less energy
- will occupy less volume
- will require lower input signal
- will probably rely on self-assembly
- Molecules might compute, sense, act and serve as building block of more complex structures.
 - Time scales
 - input- output schemes, algorithms, ...

Ĩ

Molecular Nanophotonics

Bacterio-Rhodopsin (BR): natural second and third harmonic source

Bacteriorhodopsin has a hexagonal arrangement in the purple membrane fragments and behaves as a natural photonic crystal. The helical structure embeds a retinal chromophore.



Photosynthetic Solar Cell



Molecular Nano Antenna



ECE ILLINOIS





Nanophotonic Field Enhancement



Cresyl blue SERS spectra. Adapted from Stöckle et al., Chem. Phys. Lett. 2000, 318, 131.

ECE ILLINOIS

Hybrid Nanophotonics

Inorganic-organic hybrid structures







Green spot of the SHG light is clearly observed

Fabrication of Nanophotonics

- Advanced fabrication techniques available with nanometer precision
 - Bottom-up (Chemistry)
 - Top Down (Etching, ion-milling, etc)
 - Multiple dimensions, large scale, many materials



Achieved: self-assembled structures made by binding proteins onto nodes of self assembled DNA scaffold.

Now being pursued to make ordered arrays of metallic nano-particles and ordered arrays of fluorophores.

DNA can be fabricated with predetermined sequence so offering a programmable templating tool.

The technique offers atomic resolution.

Scale bars in micrographs: 100 nm. U Oxford

Nanophotonic Bioimaging

Nanoparticles are also used for bioimaging by non-optical techniques like Magnetic Resonance Imaging (MRI), Radioactive Nanoparticles as tracers to detect drug pathways or imaging by Positron Emission Tomography (PET), and Ultrasonic Imaging. For MRI, the magnetic nanoparticles could be made of



oxide particles which are coated with some biocompatible polymer. Newer Nanoparticle Heterostructures have been investigated which offer the possibility of imaging by several techniques simultaneously. An example is Magnetic Quantum Dot.

Imaging with Dual-Labeled Probes

White-Light



γ - Scintigraphy





Multifunctional Nanoprobes-Louie: EAD289-Topics in Biophotonics, UC Davis

Ĩ

ECE ILLINOIS

Nanophotonic Bioimaging

Dual-Functional Nanoprobes for Dual-Modality Animal Imaging



Photoacoustic





T1 MRI



Bouchard and Liu et al, PNAS 2009

ECE ILLINOIS

photon particle plasmon electron-hole pair loule Heat due to



Joule Heat due to Plasmon Current



$\approx \frac{\omega}{8\pi} E_0^2 \left| \frac{3\varepsilon_{medium}}{2\varepsilon_{medium} + \varepsilon_{NP}} \right|^2 \operatorname{Im} \varepsilon_{NP}$

Temperature Increase due to Photothermal Conversion

At steady state Light Intensity $\Delta T = \frac{a_{NP}^2 Q}{3\kappa} \qquad I_0 = cE_0^2 \sqrt{\varepsilon_0} / 8\pi$ $\implies \Delta T = \frac{\omega I_0 a_{NP}^2}{3\kappa c \sqrt{\varepsilon_0}} \left| \frac{3\varepsilon_{medium}}{2\varepsilon_{medium}} + \varepsilon_{NP} \right|^2 \operatorname{Im} \varepsilon_{NP}$

NRL 1, 84-90 (2006)

Nanophotonics Therapy



H. Atwater, Scientific American 2007

Nanophotonic Molecular Manipulation



Lee et al, Nano Letter (2009)

Nanophotonic Fluidic Manipulation



Liu et al, Nature Materials (2006)

Optofluidic Molecular Manipulation





Optical Pre-Concentration of DNA



Nanophotonic Particle Manipulation



Liu et al. Manuscript in preparation

Nanophotonics Market

	2004	2009	2014
Biomedical Markers (Chapter 3)	250	360	530
Chip Interconnects (Chapter 4)	0	0	20
Optocouplers (Chapter 4)	950	1,300	
Communication Lasers (Chapters 4 and 5)	151	281	473
Communication Passives (Chapter 5)	90	189	363
Specialty Fiber (Chapter 6)	2	5	11
Biochemical Fluidic Chips (Chapter 7)	1,000	1,690	2,790
Biomedical Tool Lasers (Chapter 7)	41	64	100
LEDs (Chapter 8)	198	1,100	
Solar Cells (Chapter 9)	126	388	
Displays (Chapter 10)	31,500	49,900	
Lithography Lasers (Chapter 11)	428	553	665

Nanophotonics:

Assessment of technology and Market Opportunities

By Strategies unlimited Report OM-31, Jan. 2005

Opportunities by revenue by end products (US \$ millions)

Chip interconnects, passive components, lasers

or

Optofluidics and displays?

Nanophotonics Market



Research Trends Research needs in Nanophotonics Metamaterials Phoremost visible range Roadmap 2008 Nanoparticle-based Non-linear **Energy conversion** nano-optics Self-assembly Colloidal Photonic crystals particle engineering **Plasmonics Organic-inorganic** Optical Hybrids technologies trapping & sorting Infiltration techniques Random Nanoimprint lasers lithography Microcavities III-V / Si integration 5 years 5-10 years 10-15 years

Need for technology or material development